

2n2322 to 2n2326

SILICON THYRISTORS

All-diffused PNP thyristors designed for grating operation in mA/ μ A signal or detection circuits
Compliance to RoHS.

MAXIMUM RATINGS (*)

$T_J=125^{\circ}\text{C}$ unless otherwise noted, $R_{GK}=1000\Omega$

Symbol	Ratings	2N2322	2N2323	2N2324	2N2325	2N2326	Unit
$V_{RRM(REP)}$	Peak reverse blocking voltage (*)	25	50	100	150	200	V
$V_{RSM(NON-REP)}$	Non-repetitive peak blocking reverse voltage ($t<5.0\text{ ms}$)	40	75	150	225	300	V
$I_{T(RMS)}$	Forward Current RMS (all conduction angles)	1.6					A
I_{TSM}	Peak Surge Current (One-Half Cycle, 60Hz) No Repetition Until Thermal Equilibrium is Restored.	15					A
P_{GM}	Peak Gate Power – Forward	0.1					W
$P_{G(AV)}$	Average Gate Power - Forward	0.01					W
I_{GM}	Peak Gate Current – Forward	0.1					A
V_{GFM}	Peak Gate Voltage - Forward	6.0					V
V_{GRM}	Peak Gate Voltage - Reverse	6.0					V
T_J	Operating Junction Temperature Range	-65 to +125					$^{\circ}\text{C}$
T_{STG}	Storage Temperature Range						

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ELECTRICAL CHARACTERISTICS (*)

T_J=25°C unless otherwise noted, R_{GK}=1000Ω

Symbol	Ratings		2N2322	2N2323	2N2324	2N2325	2N2326	Unit
V _{DRM}	Peak Forward Blocking Voltage (1)	Min :	25	50	100	150	200	V
I _{RRM}	Peak Reverse Blocking Current (Rated V _{DRM} , T _J =125°C)		Max : 100					μA
I _{DRM}	Peak Forward Blocking Current (Rated V _{DRM} , T _J =125°C)		Max : 100					μA
V _{TM}	Forward « on » Voltage I _{TM} =1.0 A Peak		Max : 1.5					V
	I _{TM} =3.14 A Peak T _C =85°C		Max : 2.0					
I _{GT}	Gate Trigger Current (2) Anode Voltage=6.0 Vdc R _L =100Ω		Max : 200					μA
	Anode Voltage=6.0 Vdc R _L =100Ω, T _C =-65°C		Max : 350					
V _{GT}	Gate Trigger Voltage Anode Voltage=6.0 V R _L =100Ω		Max : 0.8					V
	Anode Voltage=6.0 V R _L =100Ω, T _C =-65°C		Max : 1.0					
	V _{DRM} = Rated R _L =100Ω, T _J =125°C		Min : 0.1					
I _H	Holding Current Anode Voltage=6.0 V		Max : 2.0					mA
	Anode Voltage=6.0 V T _C =-65°C		Max : 3.0					
	Anode Voltage=6.0 V T _C =125°C		Min : 0.15					

(*) JEDEC Registered Values

(1) V_{RSM} and V_{DRM} can be applied for all types on a continuous dc basis without incurring damage.

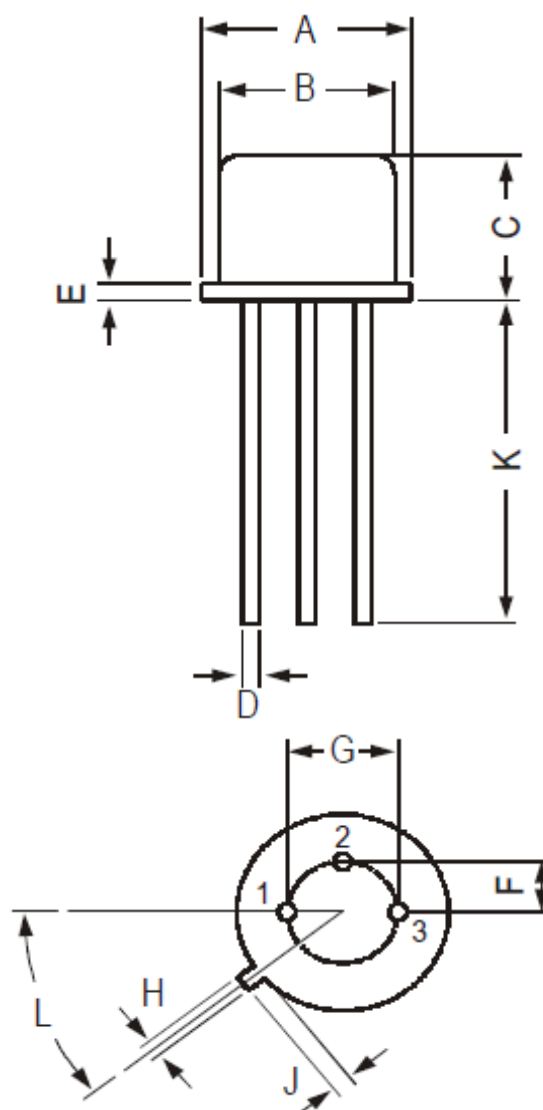
(2) R_{GK} current is not included in measurement.

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MECHANICAL DATA CASE TO-39

DIMENSIONS (mm)		
	min	max
A	8.50	9.39
B	7.74	8.50
C	6.09	6.60
D	0.40	0.53
E	-	0.88
F	2.41	2.66
G	4.82	5.33
H	0.71	0.86
J	0.73	1.02
K	12.70	-
L	42°	48°

Pin 1 :	kathode
Pin 2 :	Gate
Pin 3 :	Anode
Case :	anode



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